

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

2SK3506

Relay Drive and DC-DC Converter Applications
Motor Drive Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 16 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 26 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu\text{A}$ (max) ($V_{DS} = 30 \text{ V}$)
- Enhancement-model: $V_{th} = 1.5 \text{ to } 3.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	45	A
	Pulse (Note 1)	I_{DP}	135	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	100	W
Single pulse avalanche energy (Note 2)		E_{AS}	220	mJ
Avalanche current		I_{AR}	45	A
Repetitive avalanche energy (Note 3)		E_{AR}	10	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.25	$^\circ\text{C/W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ\text{C/W}$

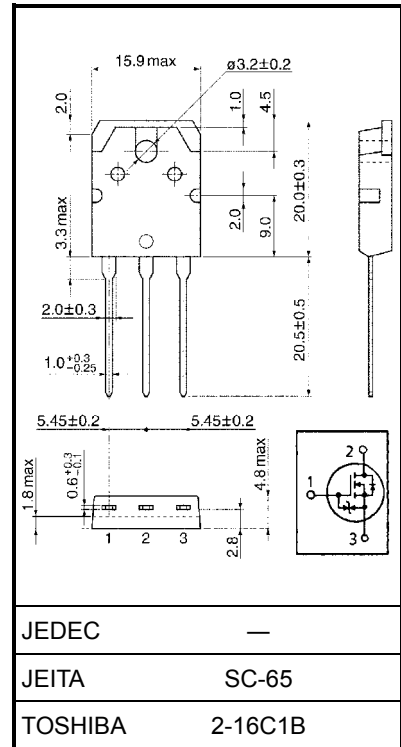
Note 1: Please use devices on condition that the channel temperature is below 150°C .

Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 78 \mu\text{H}$, $I_{AR} = 45 \text{ A}$, $R_G = 25 \Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 4.6 g (typ.)

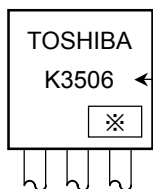
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	16	20	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	13	26	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1500	—	pF
Reverse transfer capacitance		C_{rss}		—	480	—	
Output capacitance		C_{oss}		—	680	—	
Switching time	Rise time	t_r		—	11	—	ns
	Turn-ON time	t_{on}		—	18	—	
	Fall time	t_f		—	60	—	
	Turn-OFF time	t_{off}		Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$	—	130	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 45\text{ A}$	—	39	—	nC
Gate-source charge		Q_{gs}		—	25	—	
Gate-drain ("miller") charge		Q_{gd}		—	14	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	45	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	135	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V},$	—	100	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	200	—	nC

Marking



← Type

※ Lot Number

□ □ ← Month (starting from alphabet A)

□ ← Year (last number of the christian era)

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